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Journal of Crystal Growth 193 (1998) 739–745

JOURNAL OF CRYSTAL GROWTH

Author index

Addadi, L., see Bromberg, R. 193 (1998) 656
Amano, C., K. Tateno, H. Takenouchi and Y. Ohiso, MOVPE growth of C-doped GaAs/AlAs DBRs for wafer fusion 193 (1998) 460
Ammerahl, U., G. Dhalenne, A. Revcolevschi, J. Berthon and H. Moudden, Crystal growth and characterization of the spin-ladder compound $(Sr,Ca)_{14}Cu_{24}O_{41}$ 193 (1998) 55
Anton, R., see Franke, T. 193 (1998) 451
Aswal, D.K., M. Shinmura, Y. Hayakawa and M. Kumagawa, In situ observation of melting/dissolution, nucleation and growth of $NdBa_2Cu_3O_x$ by high temperature optical microscopy 193 (1998) 61

Bakovets, V.V., Growth and wetting angles as the control parameters of crystal shape in Czochralski method 193 (1998) 720
Ballif, C., see Regula, M. 193 (1998) 109
Begarney, M.J., M.L. Warddrip, M.J. Kappers and R.F. Hicks, Kinetics of carbon tetrachloride decomposition during the metalorganic vapor-phase epitaxy of gallium arsenide and indium arsenide 193 (1998) 305
Behres, A., see Xu, J. 193 (1998) 50
Behres, A., see Xu, J. 193 (1998) 738
Berdiskihk, T., see Mei, X. 193 (1998) 148
Bernard, M.C., see Furlong, M.J. 193 (1998) 114
Berthon, J., see Ammerahl, U. 193 (1998) 55
Bettini, J., see de Castro, M.P.P. 193 (1998) 510
Bhat, A.P., see Nagaraja, H.S. 193 (1998) 674
Blanco, A., see Yates, H.M. 193 (1998) 9
Börzsönyi, T., see González-Cinca, R. 193 (1998) 712
Brandon, S., see Virozub, A. 193 (1998) 592
Brisson, O., A. Simonnet and B. Darriet and J.-C. Launay, Transmission electron microscopy investigation of $AgGaSe_2$ single crystals and study of annealing efficiency by electrical conductivity measurements 193 (1998) 597
Bromberg, R., N. Kessler and L. Addadi, Antibody recognition of specific crystal faces of 1,4-dinitrobenzene 193 (1998) 656

Buff, W., see Piechotka, M. 193 (1998) 80
Buchanan, M., see Mei, X. 193 (1998) 148
Buka, Á., see González-Cinca, R. 193 (1998) 712
Buschmann, V., S. Klein, H. Fueß and H. Hahn, HREM study of 3C–SiC nanoparticles: influence of growth conditions on crystalline quality 193 (1998) 335
Busse, P., F. Deuerler and J. Pötschke, The stability of the ODS alloy CMSX6-Al_2O_3 during melting and solidification under low gravity 193 (1998) 413

Casademunt, J., see González-Cinca, R. 193 (1998) 712
Chen, J.X., A.Z. Li, Q.K. Yang, C. Lin, Y.C. Ren, S.R. Jin, C.C. Li and M. Qi, Novel $In_{0.49}Ga_{0.51}P$/(In)GaAs/GaAs p-type modulation doped heterostructure grown by gas source molecular beam epitaxy 193 (1998) 28
Chen, Y., L.P. Guo, D.J. Johnson and R.H. Prince, Plasma-induced low-temperature growth of graphitic nanofibers on nickel substrates 193 (1998) 342
Cheng, L., see Wang, L. 193 (1998) 484
Cheng, L.-S., see Yang, H.-F. 193 (1998) 478
Cheng, X.J., see Xu, J. 193 (1998) 50
Cheng, X.J., see Xu, J. 193 (1998) 636
Cheng, X.J., see Xu, J. 193 (1998) 738
Choi, W.-J., see Kim, I. 193 (1998) 293
Chow, Y.T., see Zhang, H. 193 (1998) 370
Cortès, R., see Furlong, M.J. 193 (1998) 114
Curreri, P.A., see Sen, S. 193 (1998) 692

Dapkus, P.D., see Kim, I. 193 (1998) 293
Darriet, B., see Brisson, O. 193 (1998) 597
Dawes, J., see Zhang, H. 193 (1998) 370
De Boer, W.B., see Zhao, Q.X. 193 (1998) 328
De Carvalho, M.M., see de Castro, M.P.P. 193 (1998) 510
De Castro, M.P.P., N.C. Frateschi, J. Bettini and M.M. de Carvalho, $In_{0.49}Ga_{0.51}P$ growth on pre-patterned GaAs substrates by chemical beam epitaxy 193 (1998) 510
Deng Peizhen, see Xu Jianwei 193 (1998) 123
Deng Peizhen, see Xu Ke 193 (1998) 127

0022-0248/98/$ – see front matter © 1998 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(98)00778-7

Deuerler, F., see Busse, P. 193 (1998) 413
Dhalenne, G., see Ammerahl, U. 193 (1998) 55
Dhindaw, B.K., see Sen, S. 193 (1998) 692
Doi, Y., see Iijima, M. 193 (1998) 182
Dour, G., E. Ehret, A. Laugier, D. Sarti, M. Garnier and F. Durand, Continuous solidification of photovoltaic multicrystalline silicon from an inductive cold crucible 193 (1998) 230
Drebushchak, V.A., T.A. Kravchenko and V.S. Pavlyuchenko, Synthesis of pure pentlandite in bulk 193 (1998) 728
Duan, S.-K., see Yang, H.-F. 193 (1998) 478
Durand, F., see Dour, G. 193 (1998) 230

Eguchi, M., see Watanabe, M. 193 (1998) 402
Ehret, E., see Dour, G. 193 (1998) 230

Fang Zujie, see Xu Ke 193 (1998) 127
Feigelson, R.S., see Lee, M. 193 (1998) 347
Feigelson, R.S., see Lee, M. 193 (1998) 355
Flisch, A., see Piechotka, M. 193 (1998) 90
François, C.J.P., see Tracy, S.L. 193 (1998) 374
Franke, T., P. Kreutzer, Th. Zacher, W. Naumann and R. Anton, In situ RHEED, AFM, and REM investigations of the surface recovery of MBE-grown GaAs(0 0 1)-layers during growth interruptions 193 (1998) 451
Frateschi, N.C., see de Castro, M.P.P. 193 (1998) 510
Froment, M., see Furlong, M.J. 193 (1998) 114
Fu, Z., B. Lin, G. Liao and Z. Wu, The effect of Zn buffer layer on growth and luminescence of ZnO films deposited on Si substrates 193 (1998) 316
Fueß, H., see Buschmann, V. 193 (1998) 335
Fujii, T., see Sekijima, T. 193 (1998) 446
Fukuda, T., see Lan, C.W. 193 (1998) 552
Fukuda, T., see Kawaguchi, T. 193 (1998) 605
Furlong, M.J., M. Froment, M.C. Bernard, R. Cortès, A.N. Tiwari, M. Krejci, H. Zogg and D. Lincot, Aqueous solution epitaxy of CdS layers on $CuInSe_2$ 193 (1998) 114
Furukawa, Y., see Nabetani, Y. 193 (1998) 470

Gallagher, D.T., Q. Pan and G.L. Gilliland, Mechanism of ionic strength dependence of crystal growth rates in a subtilisin variant 193 (1998) 665
Garnier, M., see Dour, G. 193 (1998) 230
Gill, W.N., see Naik, M.B. 193 (1998) 133
Gilliland, G.L., see Gallagher, D.T. 193 (1998) 665
González-Cinca, R., L. Ramírez-Piscina, J.Casademunt, A. Hernández-Machado, T. Tóth-Katona, T. Börzsönyi and Á. Buka, Heat diffusion anisotropy in dendritic growth: phase field simulations and experiments in liquid crystals 193 (1998) 712
Goto, T., see Iijima, M. 193 (1998) 182
Grasza, K., Computational modeling of the low supersaturation nucleation in crystal growth by "contactless" physical vapor transport 193 (1998) 426
Grein, C.H., see Oh, J. 193 (1998) 241
Guillén-Cervantes, A., see López-López, M. 193 (1998) 528
Guo, L.P., see Chen, Y. 193 (1998) 342

Hahn, H., see Buschmann, V. 193 (1998) 335
Haidoux, A., see Tomasini, P. 193 (1998) 572
Han, P.-D., see Yang, H.-F. 193 (1998) 478
Hardikar, S., see Modak, P. 193 (1998) 501
Hayakawa, Y., see Aswal, D.K. 193 (1998) 61
Heime, K., see Xu, J. 193 (1998) 50
Heime, K., see Xu, J. 193 (1998) 738
Hernández-Calderón, I., see López-López, M. 193 (1998) 528
Hernández-Machado, A., see González-Cinca, R. 193 (1998) 712
Hibiya, T., see Watanabe, M. 193 (1998) 402
Hicks, R.F., see Begarney, M.J. 193 (1998) 305
Hirabayashi, I., see Takagi, A. 193 (1998) 71
Holtz, P.O., see Zhao, Q.X. 193 (1998) 328
Hondoh, T., see Salamatin, A.N. 193 (1998) 197
Hong, X., K. Lu, L. Li and D. Tang, Viscosity and density of BaB_2O_4, BaB_2O_4–NaF and BaB_2O_4–Na_2O melts 193 (1998) 610
Hozman, J., see Kubínek, R. 193 (1998) 174
Hsu, C.-T., Variation with composition of the properties in ZnS_xSe_{1-x} 193 (1998) 33
Hsu, T.C., Y. Hsu and G.B. Stringfellow, Effect of P precursor on surface structure and ordering in GaInP 193 (1998) 1
Hsu, Y., see Hsu, T.C. 193 (1998) 1
Huang, D.D., see Liu, J.P. 193 (1998) 535
Hudait, M.K., see Modak, P. 193 (1998) 501

Iga, R., see Yamamoto, N. 193 (1998) 16
Iida, K., see Takiguchi, H. 193 (1998) 641
Iijima, M., H. Kamemizu, N. Wakamatsu, T. Goto, Y. Doi and Y. Moriwaki, Effects of Ca addition on the formation of octacalcium phosphate and apatite in solution at pH 7.4 and at 37°C 193 (1998) 182
Imaeda, M., see Kawaguchi, T. 193 (1998) 605
Ishibashi, A., see Okuyama, H. 193 (1998) 43
Islam, M.R., see Saghir, M.Z. 193 (1998) 623
Itaya, A., see Nagai, Y. 193 (1998) 732

Janzén, E., see Tuominen, M. 193 (1998) 101
Jennings, H.M., see Tracy, S.L. 193 (1998) 374
Jennings, H.M., see Tracy, S.L. 193 (1998) 382
Jin, S.R., see Chen, J.X. 193 (1998) 28
Johnson, D.J., see Chen, Y. 193 (1998) 342

Kadota, Y., see Yamamoto, N. 193 (1998) 16
Kakanakova-Georgieva, A., see Tuominen, M. 193 (1998) 101

Kaldis, E., see Piechotka, M. 193 (1998) 80
Kaldis, E., see Piechotka, M. 193 (1998) 90
Kamemizu, H., see Iijima, M. 193 (1998) 182
Kang, G.Y. and J.K. Yoon, The growth of potassium lithium niobate (KLN) with low Nb_2O_5 content 193 (1998) 615
Kappers, M.J., see Begarney, M.J. 193 (1998) 305
Kauerauf, B., G. Zimmermann, L. Murmann and S. Rex, Planar to cellular transition in the system succinonitrile–acetone during directional solidification of a bulk sample 193 (1998) 701
Kaukler, W.F., see Sen, S. 193 (1998) 692
Kawaguchi, T., M. Imaeda and T. Fukuda, Selective edge-growth with controlled ferroelectric-domain structure by liquid-phase epitaxy 193 (1998) 605
Kayama, M. and J. Kuwano, Effects of the phosphorus-ion additive on the crystal habit of the emerald crystals grown from the V_2O_5–Li_2O–P_2O_5 fluxes 193 (1998) 648
Kern, R., see Müller, P. 193 (1998) 257
Kessler, N., see Bromberg, R. 193 (1998) 656
Khoo, B.C., see Ma, W.J. 193 (1998) 430
Kijima, S., see Okuyama, H. 193 (1998) 43
Kikuma, I., see Udono, H. 193 (1998) 39
Kim, C.-S., see Lee, C.-R. 193 (1998) 300
Kim, I., K. Uppal, W.-J. Choi and P.D. Dapkus, Composition control of InGaAsP in metalorganic chemical vapor deposition using tertiarybutylphosphine and tertiarybutylarsine 193 (1998) 293
Kim, T.W., D.U. Lee and Y.S. Yoon, The interfacial layer formation of the Ag/InP heterointerfaces 193 (1998) 496
Kishi, K., see Yamamoto, N. 193 (1998) 16
Klein, S., see Buschmann, V. 193 (1998) 335
Klepetsanis, P.G. and P.G. Koutsoukos, Kinetics of calcium sulfate formation in aqueous media: effect of organophosphorus compounds 193 (1998) 156
Kloc, Ch. and R.A. Laudise, Vapor pressures of organic semiconductors: α-hexathiophene and α-quaterthiophene 193 (1998) 563
Komatsu, R., see Sugawara, T. 193 (1998) 364
Kondo, Y., see Yamamoto, N. 193 (1998) 16
Kong, M.Y., see Liu, J.P. 193 (1998) 535
Kou, S., see Lin, M.H. 193 (1998) 443
Koutsoukos, P.G., see Klepetsanis, P.G. 193 (1998) 156
Kravchenko, T.A., see Drebushchak, V.A. 193 (1998) 728
Krejci, M., see Furlong, M.J. 193 (1998) 114
Kreutzer, P., see Franke, T. 193 (1998) 451
Krupanidhi, S.B., see Modak, P. 193 (1998) 501
Kubínek, R., J. Hozman and J. Vařenka, Dendritic growth in viscous solutions containing organic molecules 193 (1998) 174
Kumagawa, M., see Aswal, D.K. 193 (1998) 61
Kuwano, J., see Kayama, M. 193 (1998) 648
Kuznetsov, V.A., T.M. Okhrimenko and M. Rak, Growth promoting effect of organic impurities on growth kinetics of KAP and KDP crystals 193 (1998) 164
Kwon, Y.-S., see Leem, J.-Y. 193 (1998) 491

Lakshmanan, S.K., see Naik, M.B. 193 (1998) 133
Lan, C.W., S. Uda and T. Fukuda, Theoretical analysis of the micro-pulling-down process for Ge_xSi_{1-x} fiber crystal growth 193 (1998) 552
Laudise, R.A., see Kloc, Ch. 193 (1998) 563
Laugier, A., see Dour, G. 193 (1998) 230
Launey, J.-C., see Brisson, O. 193 (1998) 597
Lee, C.-R., J.-Y. Leem, S.-K. Noh, S.-E. Park, J.-I. Lee, C.-S. Kim, S.-J. Son and K.-Y. Leem, Characteristics of Mg-doped GaN epilayers grown with the variation of Mg incorporation 193 (1998) 300
Lee, C.-R., see Leem, J.-Y. 193 (1998) 491
Lee, D.U., see Kim, T.W. 193 (1998) 496
Lee, J.-I., see Lee, C.-R. 193 (1998) 300
Lee, J.-I., see Leem, J.-Y. 193 (1998) 491
Lee, M., R.S. Feigelson and R.K. Route, Growth of lead barium niobate ($Pb_{1-x}Ba_xNb_2O_6$) crystals by the vertical Bridgman method. I. Self-seeded growth 193 (1998) 347
Lee, M. and R.S. Feigelson, Growth of lead barium niobate ($Pb_{1-x}Ba_xNb_2O_6$) crystals by the vertical Bridgman method. II. $Sr_{0.61}Ba_{0.39}Nb_2O_6$-seeded growth 193 (1998) 355
Leem, J.-Y., see Lee, C.-R. 193 (1998) 300
Leem, J.-Y., C.-R. Lee, J.-I. Lee, S.K. Noh, Y.-S. Kwon, Y.-H. Ryu and S.-J. Son, Characteristics of Si-doped GaN compensated with Mg 193 (1998) 491
Leem, K.-Y., see Lee, C.-R. 193 (1998) 300
Lévy, F., see Regula, M. 193 (1998) 109
Li, A.Z., see Chen, J.X. 193 (1998) 28
Li, C.C., see Chen, J.X. 193 (1998) 28
Li, J.P., see Liu, J.P. 193 (1998) 535
Li, L., see Hong, X. 193 (1998) 610
Liao, G., see Fu, Z. 193 (1998) 316
Lin, B., see Fu, Z. 193 (1998) 316
Lin, C., see Chen, J.X. 193 (1998) 28
Lin, L., see Liu, X. 193 (1998) 23
Lin, M.H. and S. Kou, Czochralski pulling of InSb single crystals from a molten zone on a solid feed 193 (1998) 443
Lincot, D., see Furlong, M.J. 193 (1998) 114
Lipenkov, V.Y., see Salamatin, A.N. 193 (1998) 197
Liu, J.P., M.Y. Kong, J.P. Li, X.F. Liu, D.D. Huang and D.Z. Sun, Low-temperature growth properties of $Si_{1-x}Ge_x$ by disilane and solid-Ge molecular beam epitaxy 193 (1998) 535

Liu, X., D.-C. Lu, L. Wang, X. Wang, D. Wang and L. Lin, The dependence of growth rate of GaN buffer layer on growth parameters by metalorganic vapor-phase epitaxy 193 (1998) 23
Liu, X., see Wang, L. 193 (1998) 484
Liu, X.F., see Liu, J.P. 193 (1998) 535
Liu, Y., see Lu, T., 193 (1998) 577
López, C., see Yates, H.M. 193 (1998) 9
López-López, M., A. Guillén-Cervantes, Z. Rivera-Alvarez and I. Hernández-Calderón, Hillocks formation during the molecular beam epitaxial growth of ZnSe on GaAs substrates 193 (1998) 528
Lowndes, D.H., see Park, J.-W. 193 (1998) 516
Lu, D.-C., see Liu, X. 193 (1998) 23
Lu, D.-C., see Wang, L. 193 (1998) 484
Lu, K., see Hong, X. 193 (1998) 610
Lu, T., Y. Liu, J. Shigley, T. Moses and I.M. Reinitz, Characterization of a notable historic gem diamond showing the alexandrite effect 193 (1998) 577

Ma, W.J., B.C. Khoo and D. Xu, Influence of Coriolis force on bulk flows during horizontal Bridgman growth on a centrifuge: a numerical study 193 (1998) 430
MacMillan, M.F., see Tuominen, M. 193 (1998) 101
Maffei, N., see Saghir, M.Z. 193 (1998) 623
Matsumoto, S., see Yamamoto, N. 193 (1998) 16
Maurin, M., see Tomasini, P. 193 (1998) 572
Mawatari, H., see Yamamoto, N. 193 (1998) 16
Mei, X., H.E. Ruda, T. Berdiskihk and M. Buchanan, Liquid phase epitaxial growth of GaP layers on textured GaP (1 1 1)B substrates 193 (1998) 148
Meng, X., see Zhang, H. 193 (1998) 370
Meseguer, F., see Yates, H.M. 193 (1998) 9
Míguez, H., see Yates, H.M. 193 (1998) 9
Miyasaka, H., see Nagai, Y. 193 (1998) 732
Mizutani, U., see Takagi, A. 193 (1998) 71
Modak, P., M.K. Hudait, S. Hardikar and S.B. Krupanidhi, OMVPE growth of undoped and Si-doped GaAs epitaxial layers on Ge 193 (1998) 501
Mohan Rao, P., see Nagaraja, H.S. 193 (1998) 674
Moriwaki, Y., see Iijima, M. 193 (1998) 182
Moses, T., see Lu, T., 193 (1998) 577
Moudden, H., see Ammerahl, U. 193 (1998) 55
Müller, P. and R. Kern, Equilibrium shape of epitaxially strained crystals (Volmer–Weber case) 193 (1998) 257
Murmann, L., see Kauerauf, B. 193 (1998) 701

Nabetani, Y., K. Sawada, Y. Furukawa, A. Wakahara, S. Noda and A. Sasaki, Self-assembled InP islands grown on GaP substrate 193 (1998) 470
Nagai, Y., Y. Tsuboi, H. Miyasaka and A. Itaya, Effect of applied voltage on aggregate structure of microcrystals in vacuum-deposited films of mesogens 193 (1998) 732
Nagaraja, H.S., V. Upadhyaya, P. Mohan Rao, P. Sreeramana Aithal and A.P. Bhat, Organic nonlinear optical crystals of benzoyl glycine 193 (1998) 674
Naik, M.B., S.K. Lakshmanan, R.H. Wentorf, R.R. Reeves and W.N. Gill, Thermal chemical vapor deposition of copper from hexafluoroacetylacetonate Cu(I) vinyltrimethylsilane: kinetic studies 193 (1998) 133
Nastac, L., Analytical modeling of solute redistribution during the initial unsteady unidirectional solidification of binary dilute alloys 193 (1998) 271
Naumann, W., see Franke, T. 193 (1998) 451
Ng, G.I., see Yoon, S.F. 193 (1998) 285
Nijdam, A.J., see Plomp, M. 193 (1998) 389
Noda, S., see Nabetani, Y. 193 (1998) 470
Noh, S.K., see Lee, C.-R. 193 (1998) 300
Noh, S.K., see Leem, J.-Y. 193 (1998) 491
Nur, O., see Zhao, Q.X. 193 (1998) 328

Oh, J. and C.H. Grein, Epitaxial growth simulations of CdTe(1 1 1)B on Si(0 0 1) 193 (1998) 241
Ohiso, Y., see Amano, C. 193 (1998) 460
Ohshita, Y., M. Oshida, M. Seki and K. Watanabe, $TiSi_2$/Si interface instability in plasma-assisted chemical vapor deposition of titanium 193 (1998) 322
Okada, M., see Sekijima, T. 193 (1998) 446
Okada, Y., see Udono, H. 193 (1998) 39
Okamoto, H., see Yamamoto, N. 193 (1998) 16
Okhrimenko, T.M., see Kuznetsov, V.A. 193 (1998) 164
Okuyama, H., S. Kijima, Y. Sanaka and A. Ishibashi, Study of the growth mechanism of ZnCdSe by MBE using the mass spectrometer 193 (1998) 43
Oshida, M., see Ohshita, Y. 193 (1998) 322

Pan, J., see Yuan, Y. 193 (1998) 585
Pan, Q., see Gallagher, D.T. 193 (1998) 665
Park, J.-W., C.M. Rouleau and D.H. Lowndes, Heteroepitaxial growth of n-type CdSe on GaAs(0 0 1) by pulsed laser deposition: studies of film–substrate interdiffusion and indium diffusion 193 (1998) 516
Park, S.-E., see Lee, C.-R. 193 (1998) 300
Patel, C.J., see Zhao, Q.X. 193 (1998) 328
Pavlyuchenko, V.S., see Drebushchak, V.A. 193 (1998) 728
Pemble, M.E., see Yates, H.M. 193 (1998) 9
Peters, P., see Sen, S. 193 (1998) 692

Piechotka, M., E. Kaldis, G. Wetzel, H.-J. Schneider, W. Buff, M. Tardy and H. Stanna, Kinetics of physical vapor transport at low pressure under microgravity conditions. I. DCMF flight hardware and experimental conditions 193 (1998) 80
Piechotka, M., E. Kaldis, G. Wetzel and A. Flisch, Kinetics of physical vapour transport at low pressure under microgravity conditions. II. Results of the DCMF space experiment 193 (1998) 90
Plomp, M., A.J. Nijdam and W.J.P. van Enckevort, The structure of coarse crystal surfaces: the (0 0 $\bar{1}$) face of $K_2Cr_2O_7$ crystals grown from aqueous solution as an example 193 (1998) 389
Pötschke, J., see Busse, P. 193 (1998) 413
Prince, R.H., see Chen, Y. 193 (1998) 342

Qi, M., see Chen, J.X. 193 (1998) 28
Qiu Rongsheng, see Xu Ke 193 (1998) 127
Quon, D.H.H., see Saghir, M.Z. 193 (1998) 623

Radhakrishnan, K., see Yoon, S.F. 193 (1998) 285
Rak, M., see Kuznetsov, V.A. 193 (1998) 164
Rak, M., Influence of the back-stress effect on the interstep distance and on the surface supersaturation 193 (1998) 189
Ramasamy, P., see Sankaranarayanan, K. 193 (1998) 252
Ramírez-Piscina, L., see González-Cinca, R. 193 (1998) 712
Reeves, R.R., see Naik, M.B. 193 (1998) 133
Regel, L.L., see Skudarnov, P.V. 193 (1998) 219
Regula, M., C. Ballif and F. Lévy, In situ TEM observation of nickel promoted WS_2 thin-film crystallization 193 (1998) 109
Reinitz, I.M., see Lu, T., 193 (1998) 577
Ren, Y.C., see Chen, J.X. 193 (1998) 28
Revcolevschi, A., see Ammerahl, U. 193 (1998) 55
Rex, S., see Kauerauf, B. 193 (1998) 701
Rivera-Alvarez, Z., see López-López, M. 193 (1998) 528
Rouleau, C.M., see Park, J.-W. 193 (1998) 516
Route, R.K., see Lee, M. 193 (1998) 347
Ruda, H.E., see Mei, X. 193 (1998) 148
Ryu, Y.-H., see Leem, J.-Y. 193 (1998) 491

Saghir, M.Z., M.R. Islam, N. Maffei and D.H.H. Quon, Three-dimensional modeling of $Bi_{12}GeO_{20}$ using the float zone technique 193 (1998) 623
Salamatin, A.N., T. Hondoh, T. Uchida and V.Y. Lipenkov, Post-nucleation conversion of an air bubble to clathrate air–hydrate crystal in ice 193 (1998) 197
Sanaka, Y., see Okuyama, H. 193 (1998) 43
Sankaranarayanan, K. and P. Ramasamy, Microtube-Czochralski technique (μT-CZ): a novel way of seeding the melt to grow bulk single crystal 193 (1998) 252
Sarti, D., see Dour, G. 193 (1998) 230
Sasaki, A., see Nabetani, Y. 193 (1998) 470
Sato, K., see Takiguchi, H. 193 (1998) 641
Satoh, H., see Sekijima, T. 193 (1998) 446
Sawada, K., see Nabetani, Y. 193 (1998) 470
Schneider, H.-J., see Piechotka, M. 193 (1998) 80
Schoutsen, M., see van Hoof, P.J.C.M. 193 (1998) 679
Seki, M., see Ohshita, Y. 193 (1998) 322
Sekijima, T., H. Satoh, K. Tahara, T. Fujii, K. Wakino and M. Okada, Growth of fibrous YIG single crystals by the self-adjusting solvent FZ method 193 (1998) 446
Sen, S., B.K. Dhindaw, P.A. Curreri, P. Peters and W.F. Kaukler, Measurement of interfacial undercooling in a dilute Pb–Sn alloy near the regime of morphological instability 193 (1998) 692
Shigley, J., see Lu, T., 193 (1998) 577
Shinmura, M., see Aswal, D.K. 193 (1998) 61
Simonnet, A., see Brisson, O. 193 (1998) 597
Skudarnov, P.V., L.L. Regel and W.R. Wilcox, Visualization of convection in a simulated gradient freeze cell during centrifugation 193 (1998) 219
Södervall, U., see Zhao, Q.X. 193 (1998) 328
Son, S.-J., see Lee, C.-R. 193 (1998) 300
Son, S.-J., see Leem, J.-Y. 193 (1998) 491
Sreeramana Aithal, P., see Nagaraja, H.S. 193 (1998) 674
Stanna, H., see Piechotka, M. 193 (1998) 80
Stringfellow, G.B., see Hsu, T.C. 193 (1998) 1
Sugawara, T., R. Komatsu and S. Uda, Growth and characterization of lithium tetraborate crystals grown in phase-matching directions 193 (1998) 364
Sun, D.Z., see Liu, J.P. 193 (1998) 535
Syväjärvi, M., see Tuominen, M. 193 (1998) 101

Tahara, K., see Sekijima, T. 193 (1998) 446
Takagi, A., J.-G. Wen, I. Hirabayashi and U. Mizutani, Growth mode dependence of microstructures and superconducting properties of $Nd_{1+x}Ba_{2-x}Cu_3O_y$ thick films prepared by liquid-phase epitaxy 193 (1998) 71
Takenouchi, H., see Amano, C. 193 (1998) 460
Takiguchi, H., K. Iida, S. Ueno, J. Yano and K. Sato, Heterogeneous nucleation of n-alcohol crystals from solution assisted by vapor-deposited thin films of fatty acids 193 (1998) 641
Tang, D., see Hong, X. 193 (1998) 610
Tardy, M., see Piechotka, M. 193 (1998) 80
Tateno, K., see Amano, C. 193 (1998) 460
Tédenac, J.C., see Tomasini, P. 193 (1998) 572
Teng, X.-G., see Yang, H.-F. 193 (1998) 478
Tiwari, A.N., see Furlong, M.J. 193 (1998) 114

Tomasini, P., A. Haidoux, J.C. Tédenac and M. Maurin, Methylpentacarbonylmanganese as organometallic precursor for the epitaxial growth of manganese selenide heterostructures 193 (1998) 572
Tóth-Katona, T., see González-Cinca, R. 193 (1998) 712
Tracy, S.L., C.J.P. François and H.M. Jennings, The growth of calcite spherulites from solution I. Experimental design techniques 193 (1998) 374
Tracy, S.L., D.A. Williams and H.M. Jennings, The growth of calcite spherulites from solution. II. Kinetics of formation 193 (1998) 382
Tsuboi, Y., see Nagai, Y. 193 (1998) 732
Tuominen, M., R. Yakimova, A. Kakanakova-Georgieva, M.F. MacMillan, M. Syväjärvi and E. Janzén, Investigation of domain evolution in sublimation epitaxy of SiC 193 (1998) 101

Uchida, T., see Salamatin, A.N. 193 (1998) 197
Uda, S., see Sugawara, T. 193 (1998) 364
Uda, S., see Lan, C.W. 193 (1998) 552
Udono, H., I. Kikuma and Y. Okada, Lattice parameter of ZnSe crystals grown from melt under Zn partial pressure 193 (1998) 39
Ueno, S., see Takiguchi, H. 193 (1998) 641
Upadhyaya, V., see Nagaraja, H.S. 193 (1998) 674
Uppal, K., see Kim, I. 193 (1998) 293

Van Enckevort, W.J.P., see Plomp, M. 193 (1998) 389
Van Enckevort, W.J.P., see van Hoof, P.J.C.M. 193 (1998) 679
Van Hoof, P.J.C.M., W.J.P. van Enckevort and M. Schoutsen, The growth of extremely thin crystals: a Monte Carlo study and an application to n-paraffins 193 (1998) 679
Vařenka, J., see Kubínek, R. 193 (1998) 174
Vázquez, L., see Yates, H.M. 193 (1998) 9
Virozub, A. and S. Brandon, Radiative heat transport during the vertical Bridgman growth of oxide single crystals: slabs versus cylinders 193 (1998) 592

Wakahara, A., see Nabetani, Y. 193 (1998) 470
Wakamatsu, N., see Iijima, M. 193 (1998) 182
Wakino, K., see Sekijima, T. 193 (1998) 446
Wang, C., see Zhang, H. 193 (1998) 370
Wang, D., see Liu, X. 193 (1998) 23
Wang, D., see Wang, L. 193 (1998) 484
Wang, L., see Liu, X. 193 (1998) 23
Wang, L., X. Liu, Y. Zan, D. Wang, D.-C. Lu, Z. Wang, Y. Wang, L. Cheng and Z. Zhang, The growth and characterization of GaN grown on an Al_2O_3 coated (0 0 1) Si substrate by metalorganic vapor phase epitaxy 193 (1998) 484
Wang, P., see Zhang, H. 193 (1998) 370
Wang, X., see Liu, X. 193 (1998) 23
Wang, Y., see Wang, L. 193 (1998) 484
Wang, Z., see Wang, L. 193 (1998) 484
Warddrip, M.L., see Begarney, M.J. 193 (1998) 305
Watanabe, K., see Ohshita, Y. 193 (1998) 322
Watanabe, M., M. Eguchi and T. Hibiya, Flow and temperature field in molten silicon during Czochralski crystal growth in a cusp magnetic field 193 (1998) 402
Wen, J.-G., see Takagi, A. 193 (1998) 71
Wentorf, R.H., see Naik, M.B. 193 (1998) 133
Wetzel, G., see Piechotka, M. 193 (1998) 80
Wetzel, G., see Piechotka, M. 193 (1998) 90
Wilcox, W.R., see Skudarnov, P.V. 193 (1998) 219
Willander, M., see Zhao, Q.X. 193 (1998) 328
Williams, D.A., see Tracy, S.L. 193 (1998) 382
Wu, Z., see Fu, Z. 193 (1998) 316

Xu, D., see Ma, W.J. 193 (1998) 430
Xu, J., X.J. Cheng, A. Behres and K. Heime, Calculation of lateral distribution of lattice constant for horizontal MOVPE grown quaternary alloys 193 (1998) 50
Xu, J. and X.J. Cheng, Analysis compositional homogeneity for MOVPE grown ternary alloys in the horizontal reactor with a rotating susceptor 193 (1998) 636
Xu, J., X.J. Cheng, A. Behres and K. Heime, Erratum to "Calculation of lateral distributions of lattice constant for horizontal MOVPE grown quaternary alloys". [J. Crystal Growth 193 (1998) 50] 193 (1998) 738
Xu Jianwei, Zhou Yongzong, Zhou Guoqing, Xu Ke, Deng Peizhen and Xu Jun, Growth of large-sized sapphire boules by temperature gradient technique (TGT) 193 (1998) 123
Xu Jun, see Xu Jianwei 193 (1998) 123
Xu Jun, see Xu Ke 193 (1998) 127
Xu Ke, see Xu Jianwei 193 (1998) 123
Xu Ke, Xu Jun, Deng Peizhen, Zhou Yongzong, Zhou Guoqing, Qiu Rongsheng and Fang Zujie, γ-$LiAlO_2$ single crystal: a novel substrate for GaN epitaxy 193 (1998) 127
Xu, L.B., The formation of an inhomogeneous distribution of oxygen in CZ-Si crystal: An investigation with quantum reaction–diffusion equation 193 (1998) 541

Yakimova, R., see Tuominen, M. 193 (1998) 101
Yamamoto, N., K. Kishi, Y. Kondo, S. Matsumoto, R. Iga, Y. Kadota, H. Okamoto and H. Mawatari, Ammonium sulfide

combined etching (ACE): an effective treatment for reducing impurities prior to MOVPE InP regrowth in a process using hydrocarbon gas reactive ion etching (RIE) 193 (1998) 16
Yang, H.-F., P.-D. Han, L.-S. Cheng, Z. Zhang, S.-K. Duan and X.-G. Teng, Microstructure evolution of GaN buffer layer on $MgAl_2O_4$ substrate 193 (1998) 478
Yang, Q.K., see Chen, J.X. 193 (1998) 28
Yano, J., see Takiguchi, H. 193 (1998) 641
Yates, H.M., M.E. Pemble, H. Míguez, A. Blanco, C. López, F. Meseguer and L. Vázquez, Atmospheric pressure MOCVD growth of crystalline InP in opals 193 (1998) 9
Yoon, J.K., see Kang, G.Y. 193 (1998) 615
Yoon, S.F., P.H. Zhang, H.Q. Zheng, K. Radhakrishnan and G.I. Ng, The effects of beryllium doping in InGaAlAs layers grown by molecular beam epitaxy 193 (1998) 285
Yoon, Y.S., see Kim, T.W. 193 (1998) 496
Yuan, Y. and J. Pan, The effect of vapor phase on the growth of TiC whiskers prepared by chemical vapor deposition 193 (1998) 585
Zacher, Th., see Franke, T. 193 (1998) 451
Zan, Y., see Wang, L. 193 (1998) 484
Zhang, H., X. Meng, L. Zhu, C. Wang, P. Wang, H. Zhang, Y.T. Chow and J. Dawes, Growth and laser properties of laser crystal $Nd:Gd_{0.8}La_{0.2}VO_4$ 193 (1998) 370
Zhang, H., see Zhang, H. 193 (1998) 370
Zhang, P.H., see Yoon, S.F. 193 (1998) 285
Zhang, Z., see Yang, H.-F. 193 (1998) 478
Zhang, Z., see Wang, L. 193 (1998) 484
Zhao, Q.X., O. Nur, U. Södervall, C.J. Patel, M. Willander, P.O. Holtz and W.B. de Boer, Optical study of APCVD-grown $Si_{1-x}Ge_x/Si$ quantum well structures under different post-growth annealing conditions 193 (1998) 328
Zheng, H.Q., see Yoon, S.F. 193 (1998) 285
Zhou Guoqing, see Xu Jianwei 193 (1998) 123
Zhou Guoqing, see Xu Ke 193 (1998) 127
Zhou Yongzong, see Xu Jianwei 193 (1998) 123
Zhou Yongzong, see Xu Ke 193 (1998) 127
Zhu, L., see Zhang, H. 193 (1998) 370
Zimmermann, G., see Kauerauf, B. 193 (1998) 701
Zogg, H., see Furlong, M.J. 193 (1998) 114

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Journal of Crystal Growth 193 (1998) 746–748

JOURNAL OF CRYSTAL GROWTH

Subject index

Apparatus
- for directional solidification 701
- for in situ observation of crystallization 61
- for physical vapor transport rate 80

Biological aspects
- of antibody recognition 656

Cellular growth
- of lead–tin alloys 692
- of transparent alloys 701

Computer simulation
- of low supersaturation nucleation 426
- of melt growth 592
- of micro-pulling down process 552
- of oxygen doping in silicon 541
- of phase field model 712
- of thin crystal growth 679

Constitutional supercooling
- of barium borate 610
- of dilute binary alloys 271
- of lead–tin alloys 692

Convection 90, 133, 219, 552, 692, 701

Dendritic growth
- of liquid crystals 712
- of neodymium barium cuprate 61
- of ODS-alloys 413
- of sodium chloride 174

Device characterization
- electronic materials 9, 39, 491
- nanoparticles 335
- quantum wells 328

Diffusional control
- of cadmium selenide 516
- of germanium in silicon–germanium 328
- of solid growth 197

Dissolution of
- neodymium barium cuprate 61

Electronic materials, see Device characterization

Epitaxy, see Thin film growth

Etching
- chemical 16, 305, 510
- photolithographic 510

Heat flow control
- of numerical simulation 430
- of vapor growth system 426

Hydrodynamics, see Convection

Kinetics
- of growth 80, 90, 114, 156, 164, 182, 189, 305, 342, 374, 382, 430, 470, 510, 528, 535, 577, 610
- of nucleation 156, 257, 426, 510, 610, 641
- of particle engulfment 413
- of surface processes 451
- of thin film formation 133

Lasers, crystals for
- silver gallium selenide 597
- ultraviolet 364, 370

Melt growth technique
- by Bridgman–Stockbarger method
  - of lead barium niobate 347, 355
  - of silver gallium selenide 597
  - of succionitrile 701
  - of zinc selenide 39
  - theory of heat flow 430, 592
- by Czochralski method
  - of benzil 252
  - of gadolinium lanthanum vanadate 370
  - of germanium 720
  - of indium antimonide 443
  - of lithium tetraborate 364
  - of silicon 402, 541, 720
- by floating zone method
  - of fibrous yttrium iron garnet 446
  - of strontium calcium cuprate 55
- by induction cold crucible
  - of silicon 230
- by micro-pulling down method
  - of silicon germanium 552
- by uniaxial solidification
  - of α-aluminum oxide 123, 127
  - of binary alloys 271
  - theory of convection 271

0022-0248/98/$ – see front matter © 1998 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(98)00779-9

– by zone melting
– – of bismuth germanate 623
Microgravity, growth under
– of bismuth germanate 623
– of lead–tin alloys 692
– of mercuric iodide 80, 90
Morphological stability
– of binary alloys 271, 701
– of lead–tin alloys 692
– of protein crystals 665
– of silicon–germanium surfaces 720
– of spherulitic calcite 374, 382
– of strained crystals 257
– of titanium carbide whiskers 585

Nanoparticles, see Device characterization
Nucleation
– of cadmium telluride 426
– of neodymium barium cuprate 61
Numbers
– Grashof 430
– Marangoni 552
– Peclet 133

Phase diagram, of
– iron–nickel–sulphur 728
– neodymium barium cuprate 61
Precursor, for
– biological apatite 182
– magnesium selenide 572
– silicon carbide 335
Purification
– of pentlandite 728
– of succinonitrile 701

Quantum wells, see Device characterization

Solid growth
– by recrystallization
– – of tungsten sulphide 109
Solution growth
– by constant evaporation
– – of benzoyl amino acetic acid 674
– by flux method
– – of emeralds 648
– – of neodymium barium cuprate 61, 71
– – of potassium lithium niobate 615
– – of strontium calcium cuprate 55
– – of tungsten sulphide 109
– by low temperature method
– – of cadmium sulphide 114
– – of calcium spherulites 374, 382
– – of calcium sulphate dihydrate 156
– – of copper indium diselenide 114
– – of hydroxy apatite 182
– – of n-alcohol crystals 641
– – of octacalcium phosphate 182
– – of potassium acid phthalate 164
– – of potassium bichromate 389
– – of potassium dihydrogen phosphate 164
– – theory of growth kinetics 189
– by protein supersaturation
– – of subtilisin 665
Superlattices, multilayers
– of semi-magnetic II–VI compounds 572
Surface energy determination
– of n-paraffin 679
Surface structure, of
– cellular solid–liquid interface 701
– coarse crystal faces 389
– gallium arsenide 451
– gallium indium phosphide 1
– subtilisin 665

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of zinc sulphide selenide 33
– by liquid phase epitaxy
– – of gallium phosphide 148
– – of lithium niobate 605
– – of lithium niobate tantalate 605
– – of neodymium barium cuprate 71
– by metalorganic molecular beam epitaxy
– – of indium gallium phosphide 510
– – of indium phosphide islands 470
– – of silicon germanium 535
– – theory of growth kinetics 28
– by molecular beam epitaxy
– – of indium gallium aluminum arsenide 285
– – of zinc cadmium selenide 43
– – of zinc selenide 528
– – theory
– – – of cadmium telluride growth simulation 241
– – – of mole fraction and growth rate 43
– by vapor phase epitaxy
– – theory of growth 636
– – through chemical vapor deposition
– – – of silicon carbide 335
– – – of silicon germanium 328
– – – of titanium 322
– – through evaporation and condensation
– – – of gallium arsenide 451
– – – of silver on indium phosphide 496
– – through metalorganic chemical vapor deposition
– – – of aluminum arsenide 460
– – – of aluminum gallium arsenide 460
– – – of gallium arsenide 460, 501
– – – of gallium indium phosphide 1
– – – of gallium nitride 23, 127, 300, 478, 484, 491
– – – of indium gallium arsenide phosphide 293
– – – of indium phosphide 9, 16
– – – of indium phosphide antimonide 50
– – – of lithium aluminate 127
– – – of magnesium selenide 572

– – – of III–V compounds 305
– – – of zinc magnesium sulphide selenide 50
– – through pulsed laser deposition
– – – of cadmium selenide 516
– – through sputtering
– – – of zinc oxide 316

Vapor growth technique
– by chemical vapor deposition
– – of copper 133
– by evaporation and condensation
– – of α-hexathiophene 563
– – of α-quaterthiophene 563
– – of gallium arsenide 451
– – of mercuric iodide 80, 90
– – of organic films 732
– – of silicon carbide 101
– by plasma assisted chemical vapor deposition
– – of graphitic nanofibres 342
– by pulsed laser deposition
– – of cadmium selenide 516
– by sputtering
– – of zinc oxide 316
– theory of nucleation 426
Vapor–liquid–solid growth
– of pentlandite 728
– of titanium carbide whiskers 585
– of zinc selenide whiskers 528

Whiskers growth
– of titanium carbide 585
– of zinc selenide 528